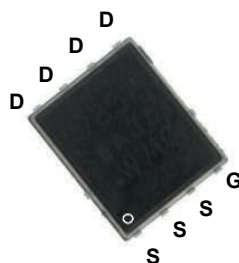
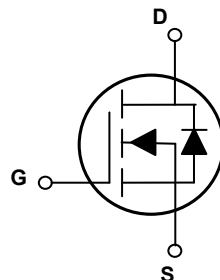


Main Product Characteristics

$V_{(BR)DSS}$	40V
$R_{DS(ON)}$	2.1m Ω (max.)
I_D	129A



PPAK5x6



Schematic Diagram

Features and Benefits

- Advanced MOSFET process technology
- Ideal for high efficiency switched mode power supplies
- Low on-resistance with low gate charge
- Fast switching and reverse body recovery
- AEC-Q101 qualified



Description

The GSGP2R104AU utilizes the latest techniques to achieve high cell density and low on-resistance. These features make this device extremely efficient and reliable for use in high efficiency switch mode power supplies and a wide variety of other applications.

Absolute Maximum Ratings ($T_J=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Parameter	Unit
Drain-Source Voltage	V_{DS}	40	V
Gate-to-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current, @ Steady-State ($T_C=25^{\circ}\text{C}$)	I_D	129	A
Continuous Drain Current, @ Steady-State ($T_C=100^{\circ}\text{C}$)		81	A
Pulsed Drain Current ²	I_{DM}	516	A
Power Dissipation ($T_C=25^{\circ}\text{C}$) ³	P_D	93	W
		0.62	W/ $^{\circ}\text{C}$
Single Pulse Avalanche Energy ¹	E_{AS}	105	mJ
Single Pulse Avalanche Current	I_{AS}	46	A
Thermal Resistance, Junction-to-Ambient (PCB Mounted, Steady-State)	$R_{\theta JA}$	50	$^{\circ}\text{C/W}$
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	1.88	$^{\circ}\text{C/W}$
Operating Junction and Storage Temperature Range	T_J/T_{STG}	-55 to +175	$^{\circ}\text{C}$
Soldering Temperature	T_{solder}	260	$^{\circ}\text{C}$

Electrical Characteristics (T_J=25°C unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
On / Off Characteristics						
Drain-to-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} =0V, I _D =250μA	40	-	-	V
Drain-to-Source Leakage Current	I _{DSS}	V _{DS} =40V, V _{GS} =0V, T _J =25°C	-	-	1.0	μA
		V _{DS} =40V, V _{GS} =0V, T _J =125°C	-	1.0	-	μA
Gate-to-Source Forward Leakage	I _{GSS}	V _{DS} =0V, V _{GS} =20V	-	-	100	nA
		V _{DS} =0V, V _{GS} =-20V	-	-	-100	
Static Drain-to-Source On-Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =50A	-	1.6	2.1	mΩ
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	1.2	-	2.6	V
Dynamic and Switching Characteristics						
Input Capacitance	C _{iss}	V _{GS} =0V, V _{DS} =25V, f=1MHz	-	2612	-	pF
Output Capacitance	C _{oss}		-	926	-	
Reverse Transfer Capacitance	C _{rss}		-	42	-	
Total Gate Charge ^{4,5}	Q _g	I _D =50A, V _{DD} =20V, V _{GS} =10V	-	43	-	nC
Gate-to-Source Charge ^{4,5}	Q _{gs}		-	13	-	
Gate-to-Drain ("Miller") Charge ^{4,5}	Q _{gd}		-	6.4	-	
Gate Plateau ^{4,5}	V _{plateau}		-	4.6	-	V
Turn-On Delay Time ^{4,5}	t _{d(on)}	V _{DD} =20V, V _{GS} =10V, R _G =4.7Ω, I _D =50A	-	12	-	nS
Rise Time ^{4,5}	t _r		-	56	-	
Turn-Off Delay Time ^{4,5}	t _{d(off)}		-	42	-	
Fall Time ^{4,5}	t _f		-	12	-	
Gate Resistance	R _g	f=1MHz	-	1.1	-	Ω
Source-Drain Ratings and Characteristics						
Continuous Source Current (Body Diode)	I _S	MOSFET symbol showing the integral reverse p-n junction diode.	-	-	129	A
Diode Pulse Current	I _{S,pulse}		-	-	516	A
Diode Forward Voltage	V _{SD}	I _S =50A, V _{GS} =0V	-	-	1.4	V
Reverse Recovery Time ⁴	T _{rr}	I _S =25A, V _{GS} =0V, V _R =20V, dI _F /dt=100A/us	-	48	-	nS
Reverse Recovery Charge ⁴	Q _{rr}		-	46	-	nC

Notes:

1. L=0.1mH, V_{DD}=32V, R_G=25Ω, starting temperature T_J=25°C.
2. Pulse time of 5μs.
3. The dissipated power value will change with the temperature. When it is greater than 25°C, the dissipated power value will decrease by 0.55°C/W for every 1 degree of temperature increase.
4. Pulse test: Pulse width ≤ 300μs, duty cycle ≤ 2%.
5. Basically unaffected by operating temperature.

Typical Electrical and Thermal Characteristic Curves

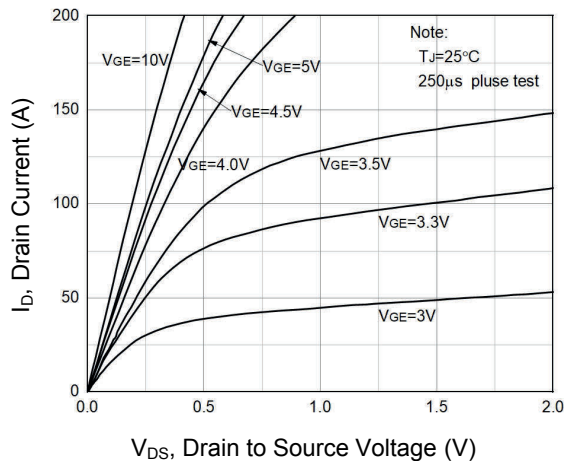


Figure 1. Typical Output Characteristics

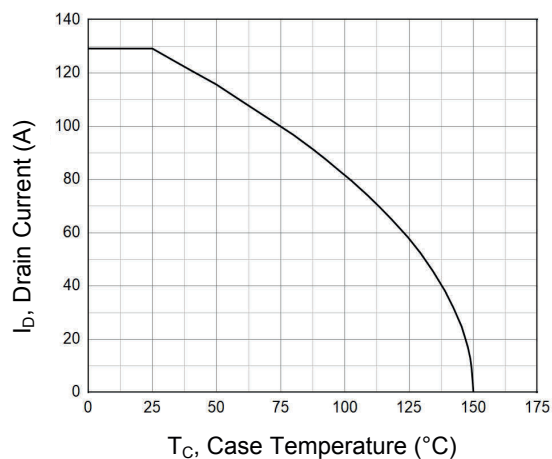


Figure 2. Drain Current vs. T_C

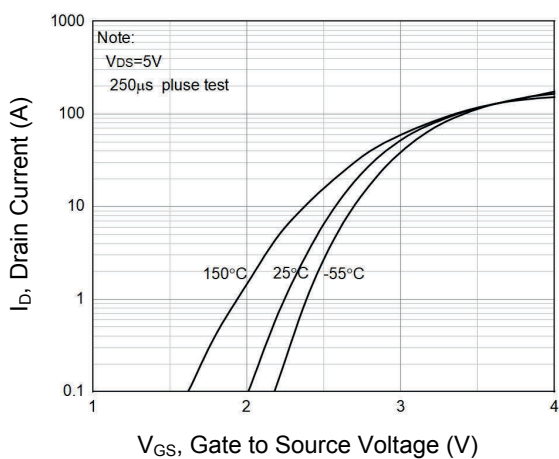


Figure 3. Transfer Characteristics

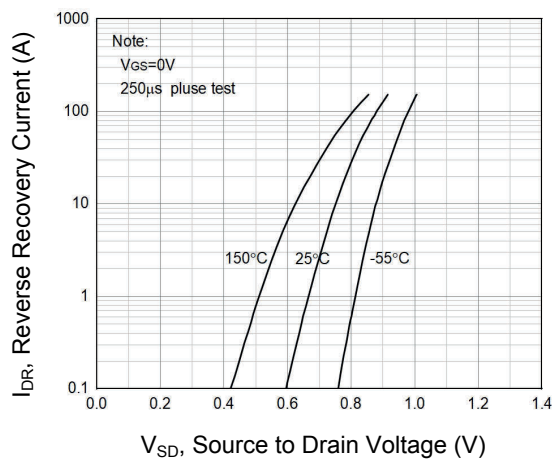


Figure 4. Body Diode Characteristics

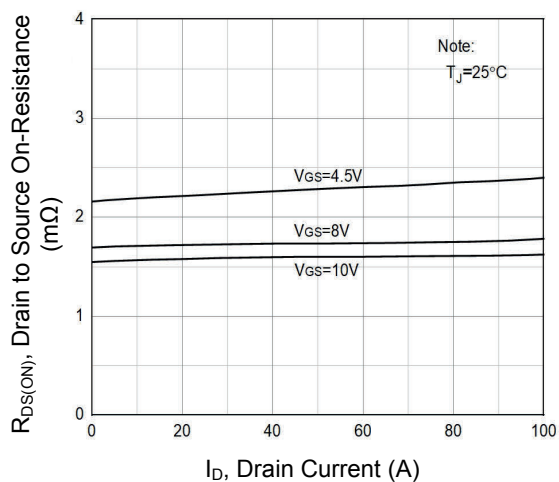


Figure 5. $R_{DS(ON)}$ vs. Drain Current

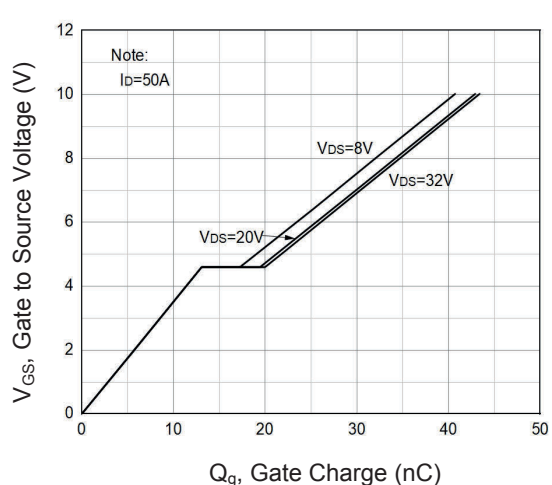


Figure 6. Gate Charge Characteristics

Typical Electrical and Thermal Characteristic Curves

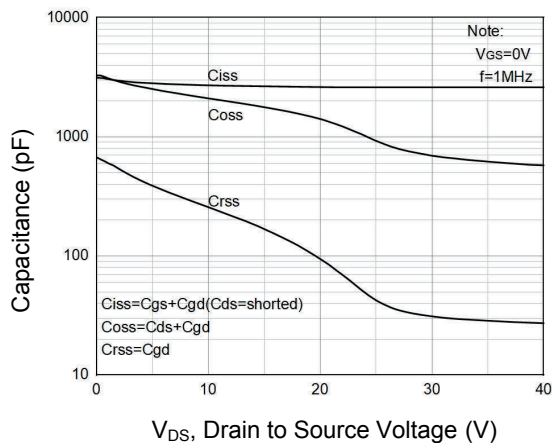


Figure 7. Capacitance Characteristics

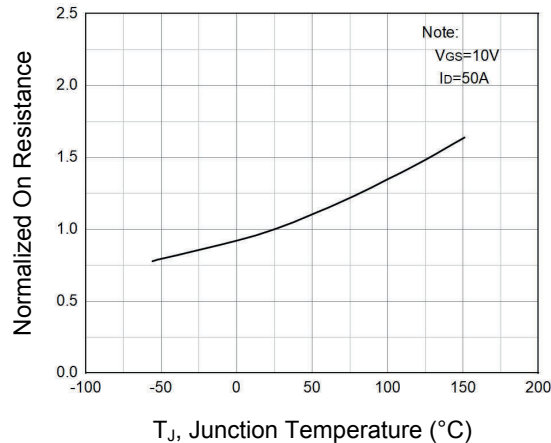


Figure 8. Normalized $R_{DS(ON)}$ vs. T_J

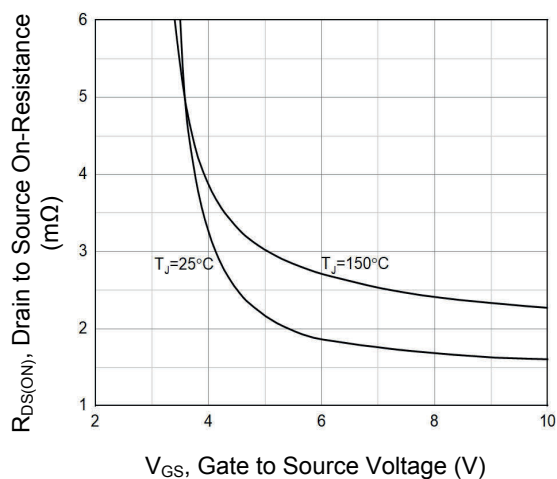


Figure 9. $R_{DS(ON)}$ vs. V_{GS}

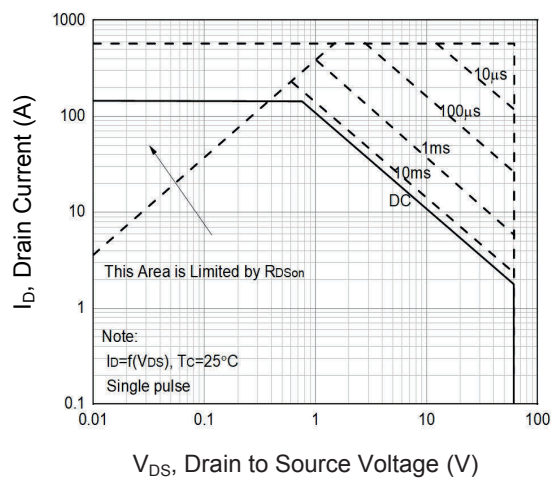


Figure 10. Safe Operation Area

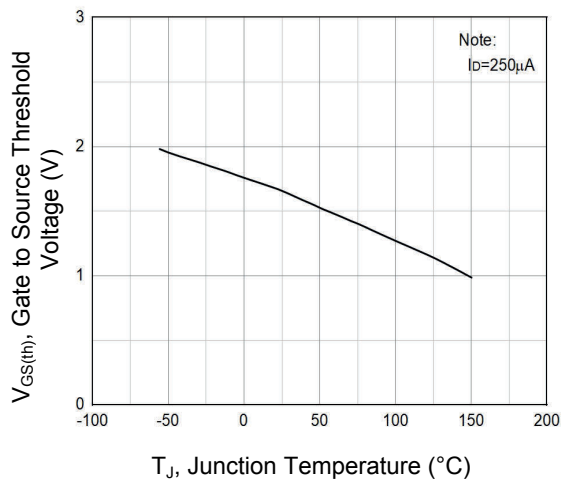


Figure 11. Gate Threshold Voltage vs. T_J

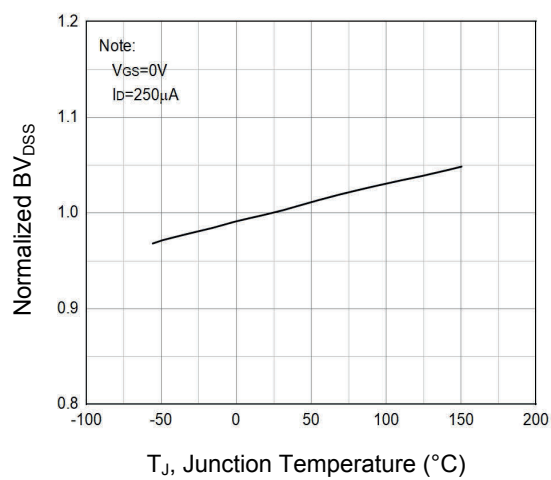
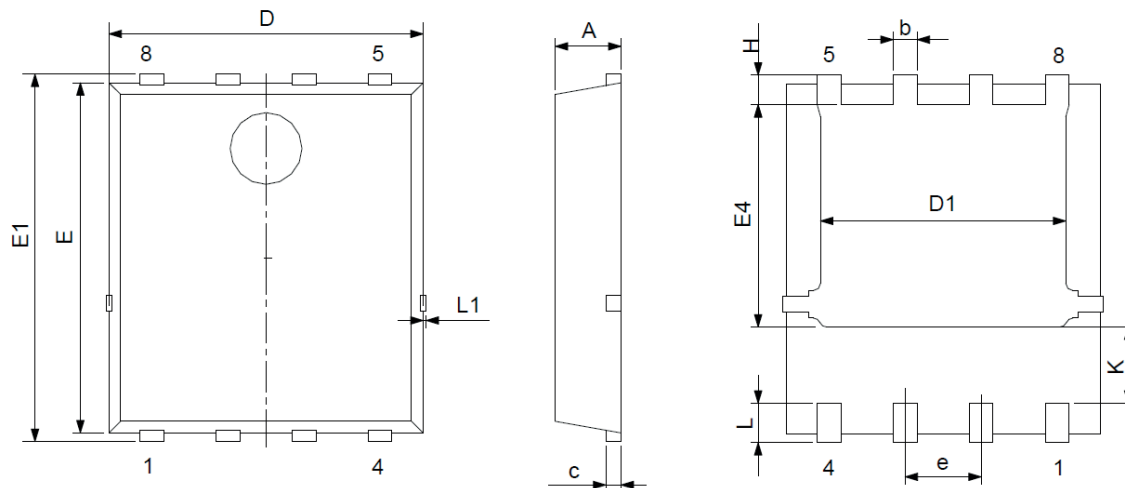


Figure 12. Normalized BV_{DS} vs. T_J

Package Outline Dimensions (PPAK5x6)



Symbol	Dimensions in Millimeters		Dimensions in Inches	
	Min	Max	Min	Max
A	0.900	1.200	0.035	0.047
c	0.154	0.354	0.006	0.014
D	4.800	5.400	0.190	0.213
E	5.660	6.060	0.223	0.240
D1	3.760	4.300	0.148	0.169
E1	5.900	6.350	0.232	0.250
b	0.300	0.550	0.012	0.022
k	1.100	1.500	0.043	0.059
e	1.070	1.370	0.042	0.054
E4	3.340	3.920	0.131	0.154
L	0.300	0.710	0.012	0.028
L1	-	0.120	-	0.005
H	0.400	0.710	0.016	0.028

Order Information

Device	Package	Marking	Carrier	Quantity
GSGP2R104AU	PPAK5x6	P2R104	Tape & Reel	5,000 Pcs / Reel